

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	1.1Ω@4V	260mA
	1.4Ω@2.5V	

Feature

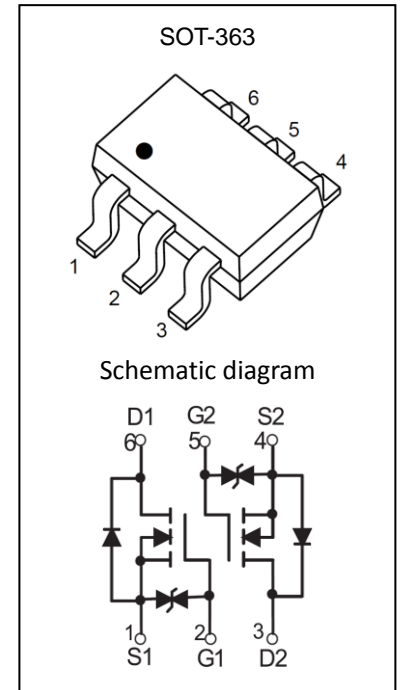
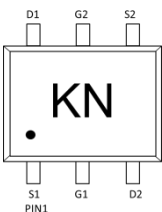
- Dual N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package

APPLICATION

- DC-DC Converters
- Power management functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories,

Transistors, etc

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ¹	I_D	260	mA
Total Power Dissipation ¹	P_D	310	mW
Thermal Resistance from Junction to Ambient ¹	$R_{\theta JA}$	411	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~ +150	°C

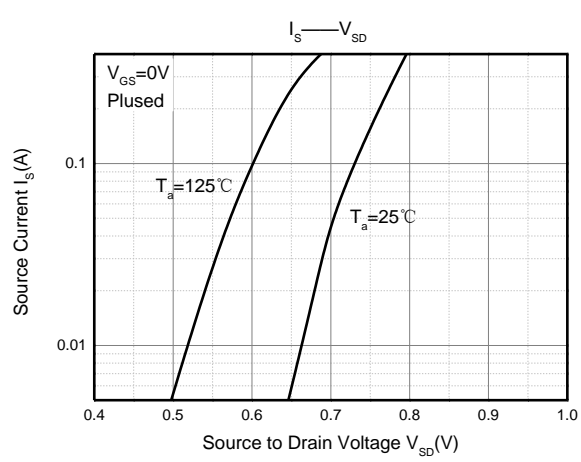
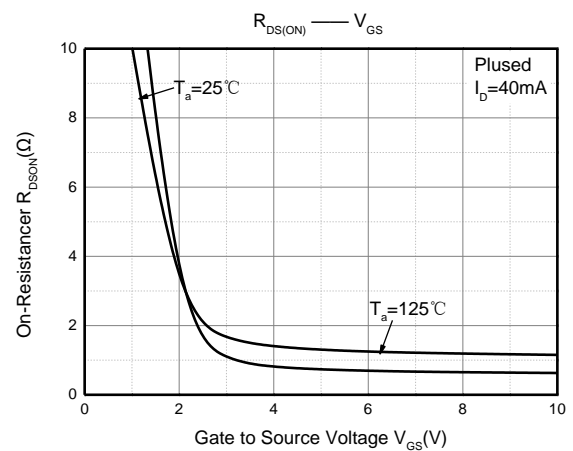
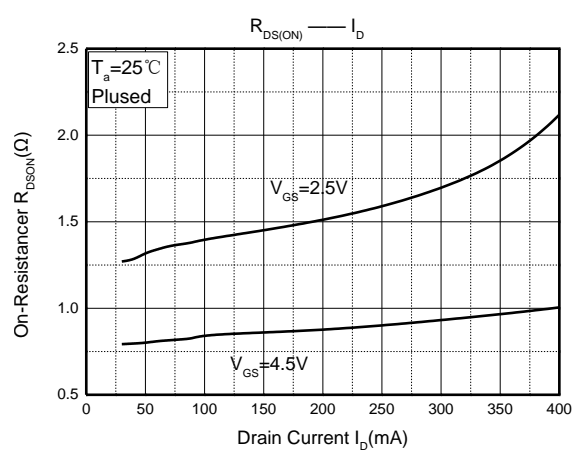
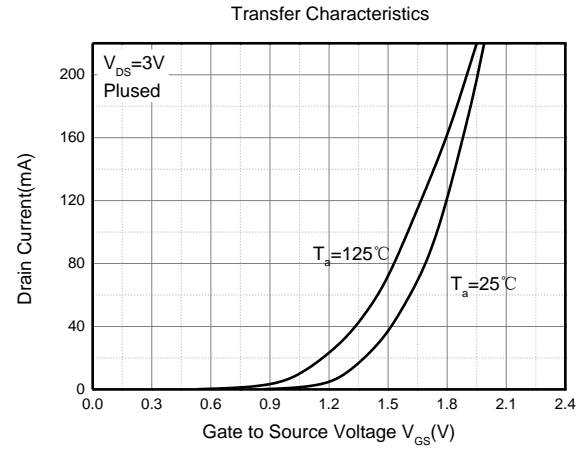
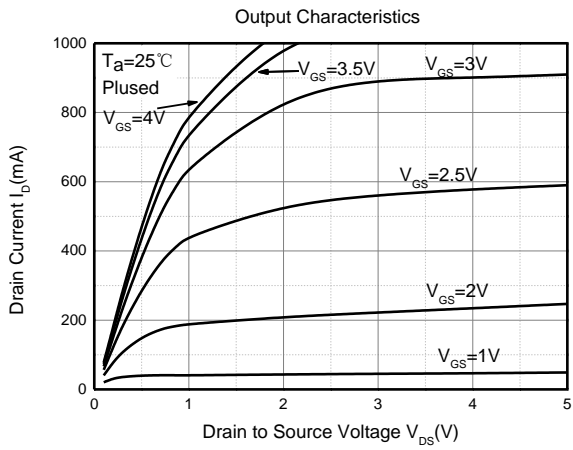
MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics²						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	50			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 50V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.7		1.5	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 4.0V, I_D = 10mA$		1.1	3.0	Ω
		$V_{GS} = 2.5V, I_D = 1mA$		1.4	4.2	
Forward transconductance	g_{FS}	$V_{DS} = 3V, I_D = 10mA$		100		mS
Diode Forward voltage	V_{DS}	$I_S = 350mA, V_{GS} = 0V$		1.0	1.2	V
Dynamic characteristics³						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$		47		pF
Output Capacitance	C_{oss}			5.5		
Reverse Transfer Capacitance	C_{rss}			4.5		
Total Gate Charge	Q_g	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250mA$		0.8		nC
Gate-Source Charge	Q_{gs}			0.4		
Gate-Drain Charge	Q_{gd}			0.2		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30V, V_{GS} = 10V,$ $R_G = 25\Omega, I_D = 200mA$		2.9		ns
Turn-on rise time	t_r			2.7		
Turn-off delay time	$t_{d(off)}$			20		
Turn-off fall time	t_f			12		

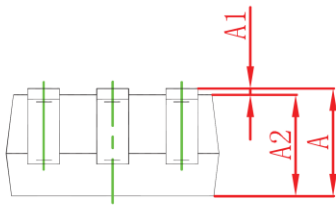
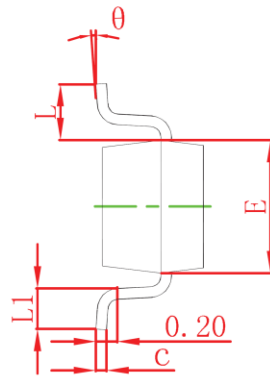
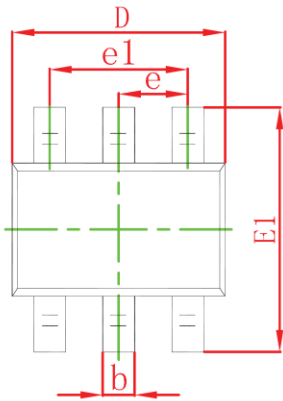
Notes:

1. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
2. Short duration pulse test used to minimize self-heating effect.
3. Guaranteed by design. Not subject to product testing.

Typical Electrical and Thermal Characteristic



SOT-363 Package Information

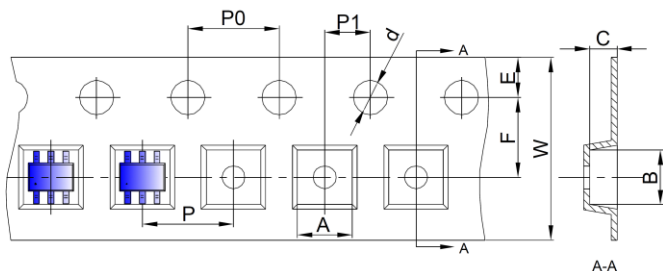


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-363 Tape and Reel

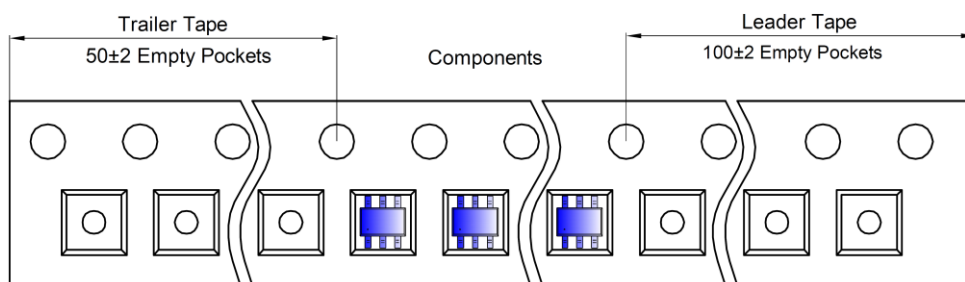
SOT-363 Tape and reel

SOT-363 Embossed Carrier Tape

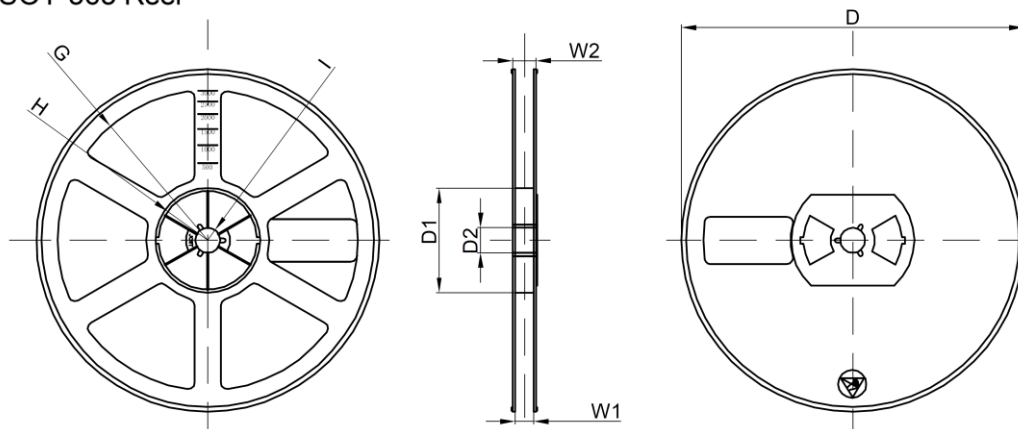


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-363	2.25	2.55	1.20	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-363 Tape Leader and Trailer



SOT-363 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)